Elektronische Bauelemente

BCX52

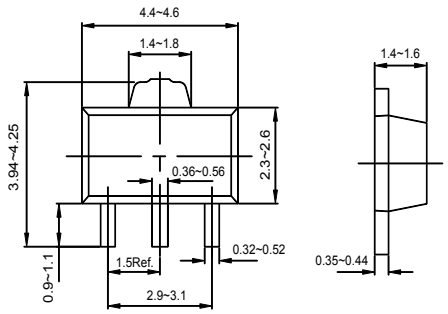
PNP Transistors

Plastic-Encapsulate Transistors

RoHS Compliant Product

1.BASE
2.COLLECTOR
3.EMITTER

SOT-89



Dimension in Millimeter

Features

Power dissipation

P_{CM}: 0.5 W (Tamb=25°C)

Collector current

I_{CM}: -1 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55°C to +150°C

ELECTRICAL CHARACTERISTICS (Tamb=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-100μA , I_E=0	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA , I_B=0	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}=-30V, I_E=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0		-0.1	μA
DC current gain **BCX52** **BCX52-10** **BCX52-16**	$h_{FE(1)}$	V_{CE}=-2V, I_C=-150mA	63 63 100	250 160 250	
	$h_{FE(2)}$	V_{CE}=-2V, I_C= -5mA	63		
	$h_{FE(3)}$	V_{CE}=-2V, I_C=-500mA	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500 mA, I_B=-50mA		-0.5	V
Base-emitter voltage	$V_{BE(ON)}$	I_C=- 500mA, V_{CE}=-2V		-1	V
Transition frequency	f_T	V_{CE}= -5V, I_C= -10mA f = 100MHz	50		MHz

DEVICE MARKING	BCX52=AE BCX52-10=AG BCX52-16=AM